

## silicon transistors

UHF/VHF power transistors  
NPN type

T-37-01

Type	Rated Breakdown Voltages			Power Out				C <sub>OB</sub> (pF)	f <sub>P</sub> (MHz)	Case
	V <sub>CB</sub>	V <sub>CE</sub>	V <sub>EB</sub>	V <sub>CE</sub>	f <sub>o</sub> (MHz)	P <sub>IE</sub> (W)	P <sub>O</sub> (W)			
2N3375	65	40	4.0	28	400	1.0	3.0	12.0	500 Typ	TO-60
2N3553	65	40	4.0	28	175	.25	2.5	12.0	350	TO-5
2N3632	65	40	4.0	28	175	3.5	13.5	25.0	250	TO-60
2N3733	65	40	4.0	28	400	4.0	10.0	25.0	250	TO-60
2N3866	55	30	3.5	28	400	0.1	1.0	3.0	500	TO-5
2N3924	36	18	4.0	13.6	175	1.0	4.0	20.0	250	TO-5
2N3928	36	18	4.0	13.6	175	2.0	7.0	20.0	250	TO-60
2N3927	36	18	4.0	13.6	175	4.0	12.0	45.0	200	TO-60
2N4012	65	40	4.0	13.6	1000	1.0	2.5	10.0	350	TO-60
2N4040	60	40	4.0	28	400	3.0	8.0	15.0	400	MT-72j
2N4041	60	40	4.0	28	400	1.0	3.3	8.0	400	MT-72j
2N4127	60	40	4.0	25	175	2.5	13.5	25.0	300	MT-72j
2N4128	60	40	4.0	25	175	6.0	24.0	45.0	200	MT-72j
2N4427	40	20	2.0	12	175	0.1	1.0	4.0	500	TO-5
2N4428	55	35	3.5	28	500	.075	.75	3.5	700	TO-5
2N4429	55	35	3.5	28	1000	.25	1.0	3.5	700	MT-72j
2N4430	55	40	3.5	28	1000	.7	2.5	5.0	600	MT-66
2N4431	55	40	3.5	28	1000	1.15	5.0	10.0	600	MT-66
2N4440	65	40	4.0	28	400	1.7	5.0	12.0	500 Typ	TO-60

Type	Rated Breakdown Voltages			Power Out				C <sub>OB</sub> (pF)	f <sub>P</sub> (MHz)	Case
	V <sub>CB</sub>	V <sub>CE</sub>	V <sub>EB</sub>	V <sub>CE</sub>	f <sub>o</sub> (MHz)	P <sub>IE</sub> (W)	P <sub>O</sub> (W)			
2N4933	70	35	4.0	24	70	3.5	20.0	85.0	200	TO-60
2N5016	65	30	4.0	28	400	5.0	15.0	25.0	500	TO-60
2N5070	65	30	4.0	28	30	.625	12.5	85	100	TO-60
2N5071	65	30	4.0	24	70	3.0	24.0	85	100	TO-60
2N5090	55	30	3.5	28	400	0.2	1.2	3.5	500	TO-60
2N5102	55	30	3.5	28	400	0.2	1.2	3.5	500	TO-60
2N5108	55	30	3.0	28	1000	.316	1.0	3.0	1200	TO-5
2N5109	40	20	3.0	28	1000	.32	1.0	3.5	1200	TO-5
2N5421	36	18	4.0	13.5	175	.125	1.0	5.0	300	TO-5
2N5423	36	18	4.0	13.5	175	1.25	5.0	25.0	300	TO-60
2N5424	36	18	4.0	13.5	175	4.1	13.0	45.0	250	TO-60
2N5591	36	18	4.0	13.6	175	9.5	25.0	120.0	200	MT-72
2N5641	65	35	4.0	28	175	1.0	7.0	15.0	300	MT-71
2N5642	65	35	4.0	28	175	2.8	20.0	35.0	250	MT-72e
2N5643	65	35	4.0	28	175	8.0	40.0	65.0	200	MT-72e
2N6080	36	18	4.0	13.6	100	—	4	20	200	MT-72h
2N6081	36	18	4.0	13.6	100	—	15	85	200	MT-72h
2N6082	36	18	4.0	13.6	100	—	25	130	200	MT-72h
2N6083	36	18	4.0	13.6	100	—	30	130	200	MT-72h
2N6084	36	18	4.0	13.6	100	—	40	200	200	MT-72h

## germanium transistors

diffused-base MESA transistors  
ultra-high-speed switching

Type	Polarity	BVCBO	BVCES	Typ. Gain HFE	f <sub>cb</sub> Avg. mc	V <sub>sat</sub> Avg. Volts	Case
		Max. Volts	Max. Volts				
2N705	PNP	-15	-15	25	300	0.125	TO-18
2N705A	PNP	-15	-15	40	—	0.125	TO-18
2N710	PNP	-15	-15	25	300	0.125	TO-18
2N710A	PNP	-15	-15	70	—	0.125	TO-18
2N711	PNP	-12	-12	80	300	0.125	TO-18
2N711A	PNP	-15	-14	80	—	0.125	TO-18
2N711B	PNP	18	15	80	320*	0.18	TO-18
2N782	PNP	-12	-12	20	—	0.125	TO-18
2N797	NPN	20	7	40	600	0.5	TO-18
2N828	PNP	-15	-15	25	—	0.125	TO-18
2N837	PNP	12	12	30	—	0.18	TO-18
2N855	NPN	12	11	30	1000	0.3	TO-18
2N855A	NPN	12	11	30	1000	0.3	TO-18
2N860	PNP	15	15	20	460*	0.125	TO-18
2N861	PNP	12	12	20	460*	0.125	TO-18
2N862	PNP	12	12	20	460*	0.125	TO-18
2N863	PNP	12	12	20	460*	0.18	TO-18
2N864	PNP	15	15	60	460*	0.125	TO-18
2N864A	PNP	15	15	60	—	0.10	TO-18
2N865	PNP	12	12	40	460*	0.125	TO-18

Type	Polarity	BVCBO	BVCES	Typ. Gain HFE	f <sub>cb</sub> Avg. mc	V <sub>sat</sub> Avg. Volts	Case
		Max. Volts	Max. Volts				
2N866	PNP	12	12	40	460*	0.125	TO-18
2N867	PNP	12	—	40	460*	0.11	TO-18
2N868	PNP	15	15	20	320*	0.18	TO-18
2N869	PNP	12	12	17	320*	0.18	TO-18
2N870	PNP	12	12	20	320*	0.18	TO-18
2N871	PNP	7	7	20	320*	0.18	TO-18
2N872	PNP	15	15	40	320*	0.18	TO-18
2N873	PNP	12	12	40	320*	0.18	TO-18
2N874	PNP	12	12	40	320*	0.18	TO-18
2N875	PNP	7	7	40	320*	0.18	TO-18
2N885	PNP	15	—	40	—	0.10	TO-18
2N894	PNP	15	15	45	—	0.18	TO-18
2N1602	PNP	25	25	10	500	0.4	TO-102
2N1693	PNP	25	25	9	450	0.4	TO-102
2N2188	PNP	40	40	80	60	—	TO-1
2N2189	PNP	40	40	80	102	—	TO-1
2N2190	PNP	60	60	80	60	—	TO-1
2N2191	PNP	60	60	80	102	—	TO-1
2N2482	NPN	20	12	15	600	2.	TO-18

## case outline drawings



